

Silicon Carbide (SiC) Schottky Diode - EliteSiC, 20 A, 650 V, D2, D2PAK-3L

FFSB2065BDN-F085

Description

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size & cost.

Features

- Max Junction Temperature 175°C
- Avalanche Rated 49 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery/No Forward Recovery
- AEC-Q101 Qualified and PPAP Capable

Applications

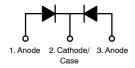
- Automotive BEV-EV
- Automotive HEV-EV Onboard Chargers
- Automotive HEV-EV DC-DC Converters

MOSFET MAXIMUM RATINGS (T_C = 25°C unless otherwise noted)

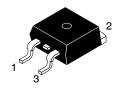
Symbol	Parameter		Ratings	Unit	
V _{RRM}	Peak Repetitive Reverse Voltage		650	V	
E _{AS}	Single Pulse Avalan	che Energy (Note 1)	49	mJ	
I _F	Continuous Recti- @ T _C < 25°C		23.6	Α	
	fied Forward Current	@ T _C < 140°C	10		
I _{F, Max}	Non-Repetitive Peak Forward	$T_C = 25^{\circ}C$, 10 µs	600	Α	
	Surge Current	$T_C = 150^{\circ}C, 10 \mu s$	554		
I _{F, SM}	Non-Repetitive Forward Surge Current, T _C = 25°C	Half-Sine Pulse, t _p = 8.3 ms	45	А	
P _{tot}	Power Dissipation	T _C = 25°C	75	W	
		T _C = 150°C	12.5		
T _J , T _{STG}	Operating and Store Range	perating and Storage Temperature ange		ô	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. E_{AS} of 49 mJ is based on starting $T_{J} = 25^{\circ}C$, L = 0.5 mH, $I_{AS} = 14$ A, V = 50 V.

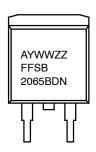


Schottky Diode



D²PAK-3 (TO-263, 3-LEAD) CASE 418AJ

MARKING DIAGRAM



= Assembly Plant Code = Date Code (Year & Week) YWW

= Lot Code

FFSB2065BDN = Specific Device Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

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THERMAL CHARACTERISTICS

Symbol	Parameter	Ratings	Unit
$R_{ heta JC}$	Thermal Resistance, Junction to Case, Max	2.0	°C/W

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted – per leg)

Symbol	Parameter	Test Conditions	Min	Тур.	Max.	Unit
V _F	Forward Voltage	I _F = 10 A, T _C = 25°C	-	1.38	1.75	V
		I _F = 10 A, T _C = 125°C	-	1.6	2.0	
		I _F = 10 A, T _C = 175°C	-	1.72	2.4	1
I _R	Reverse Current	V _R = 650 V, T _C = 25°C	-	0.5	40	μΑ
		V _R = 650 V, T _C = 125°C	-	1	80	
		V _R = 650 V, T _C = 175°C	-	2	160	
Q _C	Total Capacitive Charge	V = 400 V	-	25	-	nC
С	Total Capacitance	V _R = 1 V, f = 100 kHz	-	421	-	pF
		V _R = 200 V, f = 100 kHz	-	46	_	
		V _R = 400 V, f = 100 kHz	_	35	-	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

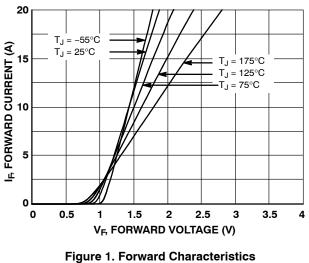
PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Mark	Package	Shipping [†]
FFSB2065BDN-F085	FFSB2065BDN	D2PAK	800 Units/ Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

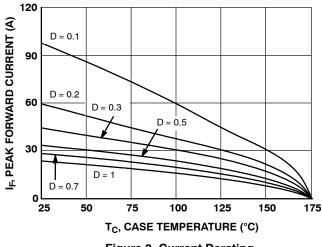
FFSB2065BDN-F085

TYPICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)



10⁻⁵ IR, REVERSE CURRENT (A) $T_J =$ 10-7 = 125°C $T_J = 25^{\circ}C$ 200 300 400 600 650 500 **V_R, REVERSE VOLTAGE (V)**

Figure 2. Reverse Characteristics



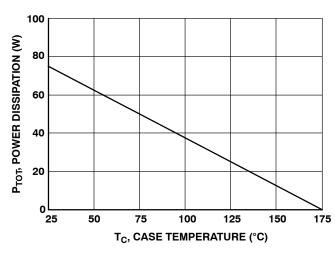
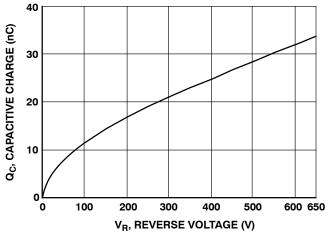


Figure 3. Current Derating

Figure 4. Power Derating



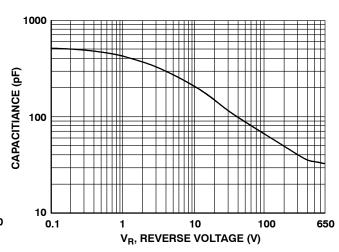


Figure 5. Capacitive Charge vs. Reverse Voltage

Figure 6. Capacitance vs. Reverse Voltage

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TYPICAL CHARACTERISTICS ($T_C = 25$ °C unless otherwise noted) (continued)

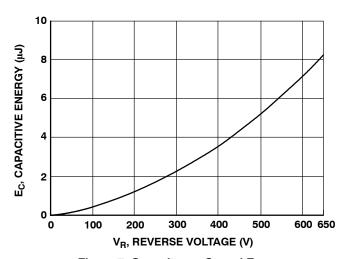


Figure 7. Capacitance Stored Energy

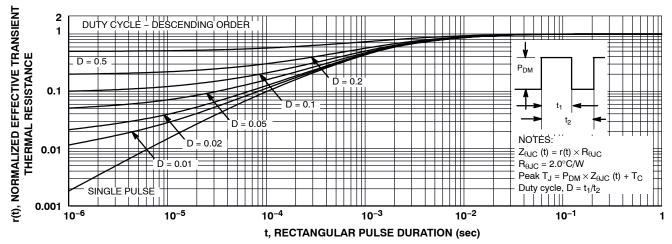


Figure 8. Junction-to-Case Transient Thermal Response Curve

TEST CIRCUIT AND WAVEFORMS

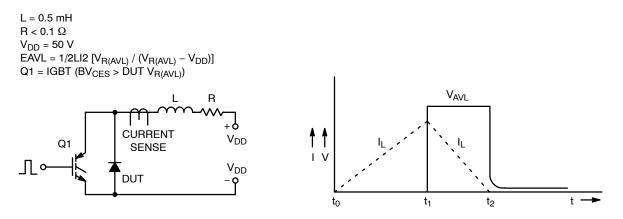
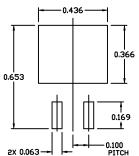


Figure 9. Unclamped Inductive Switching Test Circuit & Waveform



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DATE 11 MAR 2021



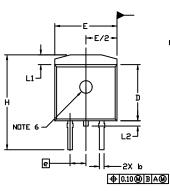
RECOMMENDED MOUNTING FOOTPRINT

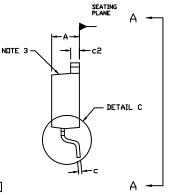
For additional information on our Pb-Free strategy and soldering details, please download the DN Seniconductor Soldering and Mounting Techniques Reference Manual, SDL DERRHYD.

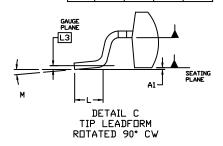
NOTES

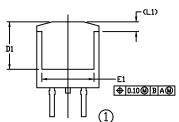
- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
- 2. CONTROLLING DIMENSION: INCHES
- 3. CHAMFER OPTIONAL.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH.
 MOLD FLASH SHALL NOT EXCEED 0.005 PER SIDE.
 THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST
 EXTREMES OF THE PLASTIC BODY AT DATUM H.
- 5. THERMAL PAD CONTOUR IS OPTIONAL WITHIN DIMENSIONS E, L1, D1, AND E1.
- 6. OPTIONAL MOLD FEATURE.
- 7. ①,② ... OPTIONAL CONSTRUCTION FEATURE CALL DUTS.

	INCHES		MILLIMETERS	
DIM	MIN.	MAX.	MIN.	MAX.
Α	0.160	0.190	4.06	4.83
A1	0.000	0.010	0.00	0.25
b	0.020	0.039	0.51	0.99
С	0.012	0.029	0.30	0.74
c2	0.045	0.065	1.14	1.65
D	0.330	0.380	8.38	9.65
D1	0.260		6.60	
Ε	0.380	0.420	9.65	10.67
E1	0.245		6.22	
e	0.100 BSC		2.54 BSC	
Н	0.575	0.625	14.60	15.88
L	0.070	0.110	1.78	2.79
L1		0.066		1.68
L2		0.070		1.78
L3	0.010 BSC		0.25 BSC	
М	0*	8*	0*	8.

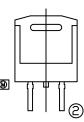


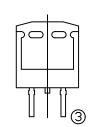


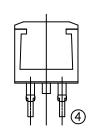




VIEW A-A



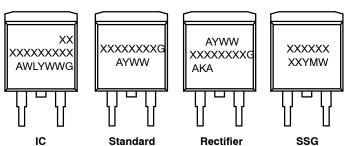




VIEW A-A

OPTIONAL CONSTRUCTIONS

GENERIC MARKING DIAGRAMS*



XXXXXX = Specific Device Code

 A
 = Assembly Location

 WL
 = Wafer Lot

 Y
 = Year

 WW
 = Work Week

 W
 = Week Code (SSG)

 M
 = Month Code (SSG)

 G
 = Pb-Free Package

 AKA
 = Polarity Indicator

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " •", may or may not be present. Some products may not follow the Generic Marking.

DOCUMENT NUMBER:

98AON56370E

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DESCRIPTION:

D²PAK-3 (TO-263, 3-LEAD)

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